



S/N 10/765,619

PATENT

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

Applicant: Kie Y. Ahn et al. Examiner: Asok K Sarkar
Serial No.: 10/765,619 Group Art Unit: 2829
Filed: January 27, 2004 Docket No.: 1303.033US2
Title: HIGH-QUALITY PRASEODYMIUM GATE DIELECTRICS (As Amended)

AMENDMENT AND RESPONSE UNDER 37 CFR § 1.111

MS Amendment
Commissioner for Patents
P.O. Box 1450
Alexandria, VA 22313-1450

This responds to the Office Action mailed on December 10, 2004. Please amend the above-identified patent application as follows.

IN THE TITLE

Please amend the title as follows:

~~LOW TEMPERATURE GROWN HIGH-QUALITY ULTRA THIN PRASEODYMIUM~~
GATE DIELECTRICS